

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-7 (Canceled).

Claim 8 (Currently Amended): A method for transferring an electrically active thin film from an initial substrate to a target substrate, comprising:

ion implantation through one face of the initial substrate to create a buried, embrittled film at a determined depth in relation to the implanted face of the initial substrate, a thin film thus being delimited between the implanted face and the buried ~~face~~ film;

fastening the implanted face of the initial substrate with a face of the target substrate;  
separating the thin film from a remainder of the initial substrate at a level of the buried film; and

thinning down the thin film transferred on the target substrate;

wherein implantation dosage, energy, ~~and~~ current and said determined depth are chosen, during the ion implantation, so that concentration of implantation defects is less than a determined threshold, resulting in, within the thinned down thin film, a number of acceptor defects that is compatible with desired electrical properties of the thin film.

Claim 9 (Previously Presented): A method according to claim 8, wherein the ion implantation includes implanting ions chosen from among the following species: hydrogen and rare gases.

Claim 10 (Previously Presented): A method according to claim 8, wherein the fastening includes a bonding chosen from bonding by molecular adhesion via intermediate

films or without intermediate films, bonding by reaction, metallic bonding, brazing or bonding by species diffusion.

Claim 11 (Previously Presented): A method according to claim 8, further comprising healing annealing of the implantation defects on the thin film.

Claim 12 (Previously Presented): A method according to claim 11, wherein the healing annealing is carried out before the thinning down the thin film.

Claim 13 (Previously Presented): A method according to claim 11, wherein the healing annealing is carried out after the thinning down the thin film.

Claim 14 (Previously Presented): Application of the method according to claim 8 to obtain a thin film of SiC, GaAs, GaN, diamond, or InP on a target substrate.

Claim 15 (New): The application of Claim 14 to obtain a thin film of SiC of a thickness less than or equal to  $0.5\text{ }\mu\text{m}$  and with a concentration of defects less than  $9\cdot 10^{20}$  atoms/cm<sup>3</sup>.